

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A high power semiconductor device ~~in which there are a plurality of~~ including gate electrodes also includes: an active region of an approximately rectangular shape ~~which is formed, located~~ on a semiconductor substrate; a drain electrode ~~which is formed~~ located on the active region; and ~~a~~ first and ~~a~~ second source electrodes which are disposed on ~~the both opposite~~ sides to the drain electrode ~~in such a manner so~~ that the first and ~~the~~ second source electrodes face each other across at least some of the gate electrodes. The directions of currents carried by the first and ~~the~~ second source electrodes are opposite to each other.